

## **BUK7275-100A**

# N-channel TrenchMOS standard level FET Rev. 02 — 17 June 2010

**Product data sheet** 

#### **Product profile**

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

#### 1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching

Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	100	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	21.7	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	89	W
Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 13 \text{ A};$ $T_j = 175 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 12}}{\text{Figure 13}};$	-	-	187	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 13 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see } \frac{\text{Figure 13}}{\text{ of } \frac{1}{2}};$	-	64	75	mΩ
Avalanche	Avalanche ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 14 \text{ A; } V_{sup} \leq 100 \text{ V;} \\ R_{GS} &= 50  \Omega; V_{GS} = 10 \text{ V;} \\ T_{j(init)} &= 25 ^{\circ}\text{C; } unclamped \end{split}$	-	-	100	mJ



### 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		G (EX)
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

### 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7275-100A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	100	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>		-	-	21.7	Α
		$T_{mb} = 100  ^{\circ}\text{C};  V_{GS} = 10  \text{V};  \text{see}  \frac{\text{Figure 1}}{}$		-	-	15.4	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p \le 10 \mu s$ ; pulsed; see Figure 3	[1]	-	-	87	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	89	W
T <sub>stg</sub>	storage temperature			-55	-	175	°C
T <sub>j</sub>	junction temperature			-55	-	175	°C
Source-drain	diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	-	21.7	Α
I <sub>SM</sub>	peak source current	$t_p \le 10 \mu\text{s}; \text{ pulsed}; T_{mb} = 25 ^{\circ}\text{C}$		-	-	87	Α
Avalanche ru	ggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 14 A; $V_{sup}$ ≤ 100 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	100	mJ

[1] Peak drain current is limited by chip, not package.

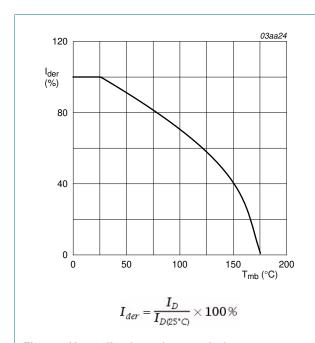
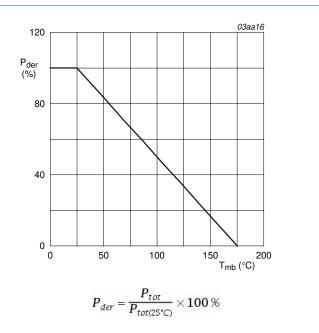
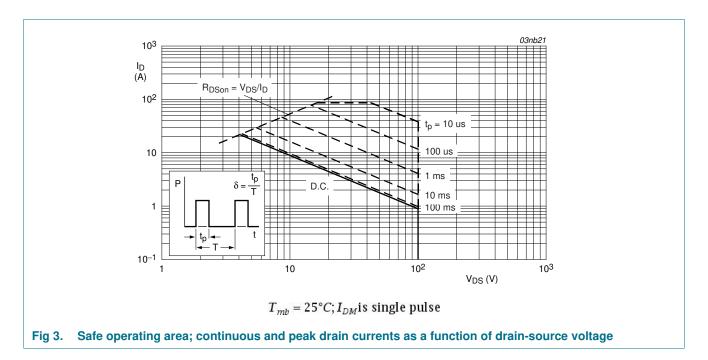


Fig 1. Normalized continuous drain current as a function of mounting base temperature



g 2. Normalized total power dissipation as a function of mounting base temperature

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#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	1.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	71.4	-	K/W

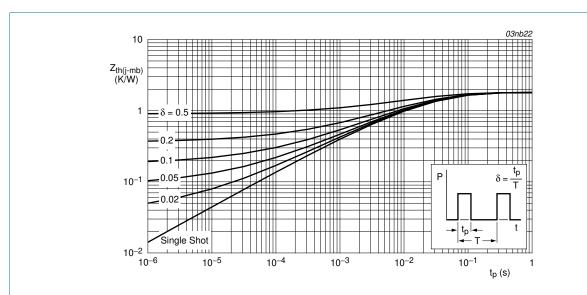


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub> drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V	
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see <u>Figure 11</u>	-	-	4.4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 11</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 11	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.05	10	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 20 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>DS</sub> = 0 V; V <sub>GS</sub> = -20 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub> drain-source resistance	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 13 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	187	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 13 A; $T_j$ = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	64	75	mΩ
Dynamic	characteristics					
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	910	1210	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	130	152	pF
$C_{rss}$	reverse transfer capacitance		-	80	107	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 2.2 \Omega; V_{GS} = 10 \text{ V};$	-	8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \Omega$ ; $T_j = 25 °C$	-	39	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	26	-	ns
t <sub>f</sub>	fall time		-	24	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain lead from package to centre of die	-	2.5	-	nΗ
L <sub>S</sub>	internal source inductance	measured from source lead from package to source bond pad	-	7.5	-	nΗ
Source-d	rain diode					
\/	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$	-	0.85	1.2	V
VSD		see <u>Figure 15</u>				
$V_{SD}$ $t_{rr}$	reverse recovery time	see <u>Figure 15</u> I <sub>S</sub> = 13 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V; T <sub>i</sub> = 25 °C	-	64	-	ns

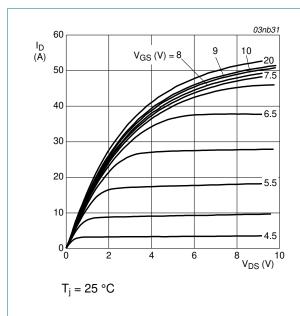


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

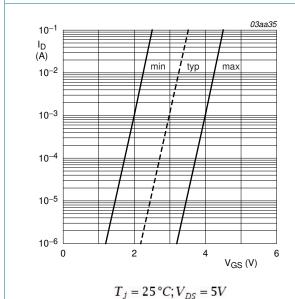
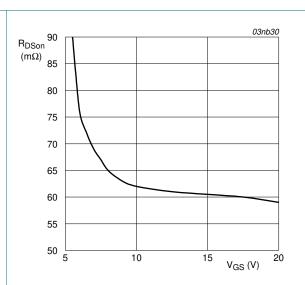
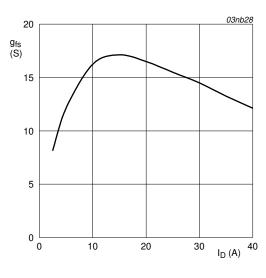


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 10A$ 

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j=25^{\circ}C; V_{DS}=25V$ 

Fig 8. Forward transconductance as a function of drain current; typical values

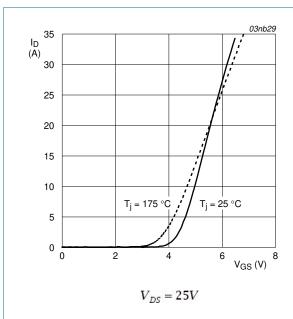


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

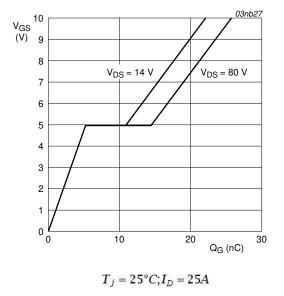


Fig 10. Gate-source voltage as a function of turn-on gate charge; typical values

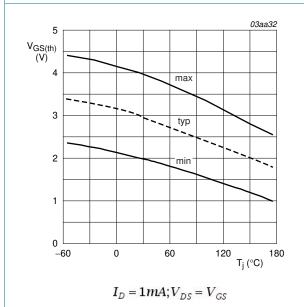


Fig 11. Gate-source threshold voltage as a function of junction temperature

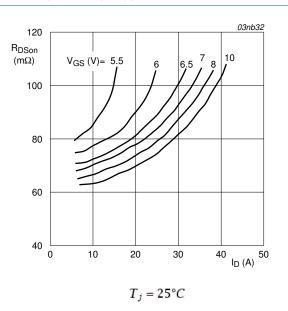


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

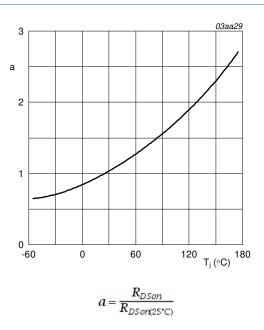


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

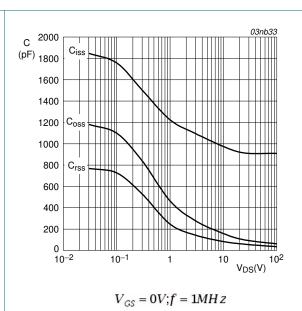


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

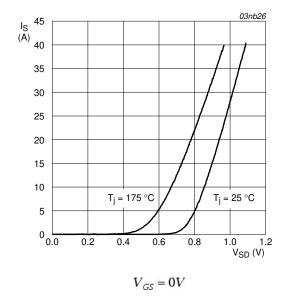


Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

#### 7. Package outline

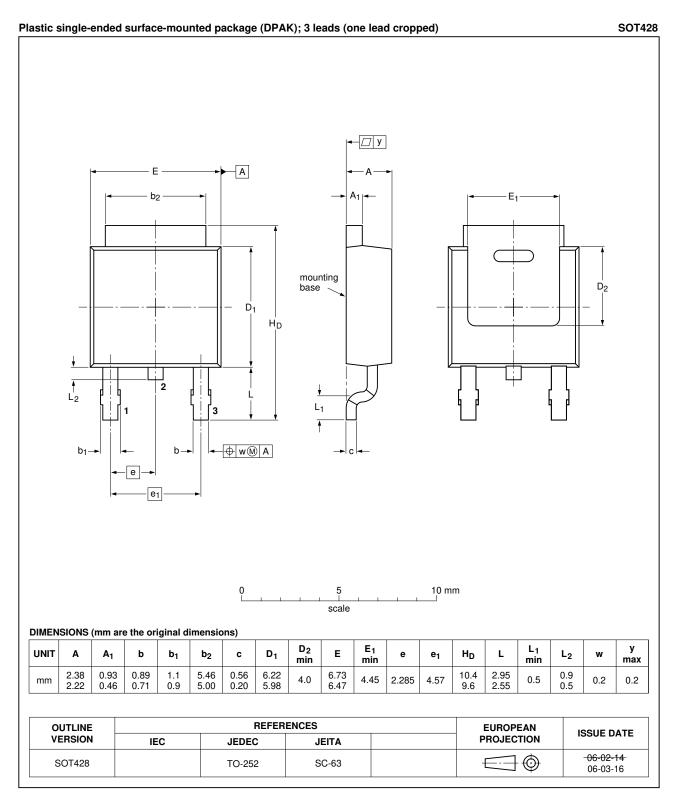


Fig 16. Package outline SOT428 (DPAK)

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### 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BUK7275-100A v.2	20100617	Product data sheet	-	BUK7275-100A v.1	
Modifications:		<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelin of NXP Semiconductors.</li> </ul>			
	<ul> <li>Legal texts</li> </ul>	have been adapted to the I	new company name where	appropriate.	
BUK7275-100A v.1 (9397 750 07645)	20001025	Product Specification	-	-	

#### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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